

isc Silicon PNP Power Transistor

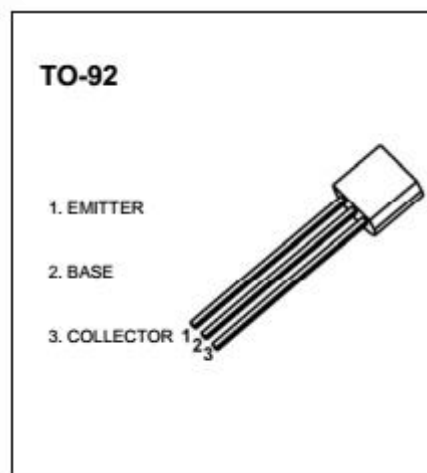
2SA562

DESCRIPTION

- Low Saturation Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation.

APPLICATIONS

- Designed for high-speed switching and Amplifier applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CB0}	Collector-Base Voltage	-35	V
V_{CE0}	Collector-Emitter Voltage	-30	V
V_{EB0}	Emitter-Base Voltage	-5	V
I_c	Collector Current-Continuous	-0.5	A
P_c	Collector Power Dissipation @ $T_c=25^{\circ}\text{C}$	0.5	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~150	$^{\circ}\text{C}$

isc Silicon PNP Power Transistor**2SA562****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-100μA, I _E =0	-35		V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA, I _B =0	-30		V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-100μA, I _C =0	-5		V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C =-100mA; I _B =-10mA		-0.25	V
V _{BE(on)}	base-emitter voltage	I _C =-100mA; V _{CE} =-1V		-1.0	V
I _{CBO}	collector cut-off current	V _{CB} =-35 V, I _E =0		-0.1	uA
I _{EBO}	Emitter Cutoff Current	V _{EB} =-5V; I _C =0		-0.1	uA
h _{FE-1}	DC Current Gain	I _C =-0.1A; V _{CE} =-1V	70	240	
h _{FE-2}	DC Current Gain	I _C =-0.4A; V _{CE} =-6V	25		

Classification of h_{FE1}

Rank	O	Y
h _{FE-1}	70-140	120-240
h _{FE-2}	25min	40min